

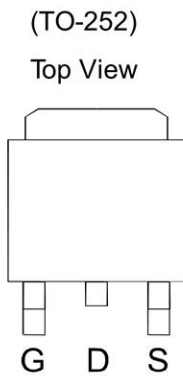
Features

- $V_{DS} -100V$
 $I_D -13A$
 $R_{DS(ON)}$ (at $V_{GS}=-10V$) $< 210m\Omega$

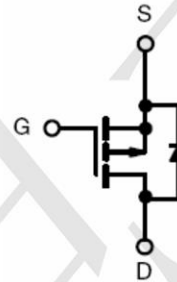
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

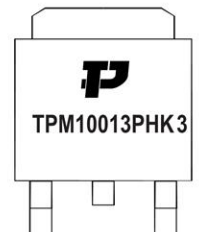
Package and Pin Configuration



1. GATE
2. DRAIN
3. SOURCE



Marking:



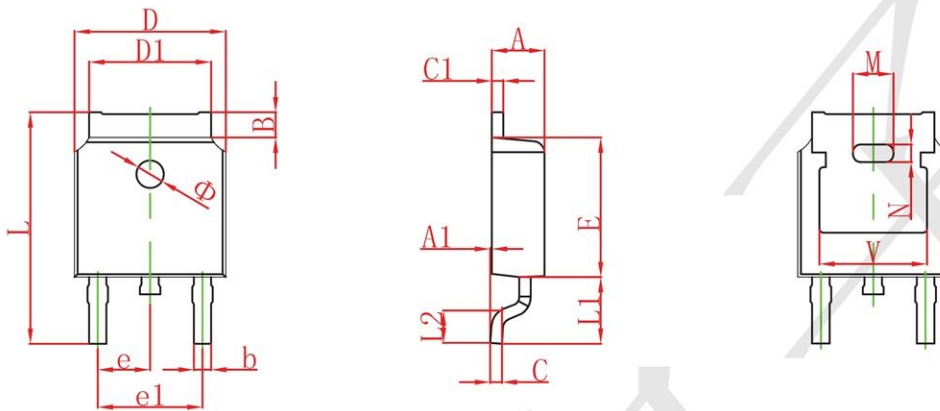
Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-13	A
Pulsed Drain Current ①	I_{DM}	-30	
Continuous Source-Drain Current(Diode Conduction)	I_S	13	
Power Dissipation ②	P_D	66	W
Thermal Resistance from Junction to Ambient ($t \leq 5s$)	$R_{\theta JA}$	110	$^\circ C/W$
Operating Junction	T_J	175	$^\circ C$
Storage Temperature	T_{STG}	-55~+175	$^\circ C$

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250μA	-100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-2		-4	V
Gate-Body leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -100V, V _{GS} = 0V			-1	μA
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -6A		180	210	mΩ
Forward Transconductance	g _{fs}	V _{DS} = -50V, I _D = -12A		3.2		S
Diode Forward Voltage	V _{SD}	I _S = -1A, V _{GS} = 0V		-0.8	-1.2	V
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} = -30V, V _{GS} = 0V, f = 1MHz		760		pF
Output Capacitance	C _{oss}			260		pF
Reverse Transfer Capacitance	C _{rss}			170		pF
Total Gate Charge	Q _g	V _{DS} = -80V, V _{GS} = - 10V, I _D = -12A		58		nC
Gate Source Charge	Q _{gs}			8.3		nC
Gate Drain Charge	Q _{gd}			32		nC
Switching Parameters						
Turn-On DelayTime	t _{d(on)}	V _{DD} = -50V R _L = 10Ω, I _D = -8.4A, V _{GEN} = -10V, R _g = 9Ω		130		ns
Turn-On Rise Time	t _r			130		ns
Turn-Off DelayTime	t _{d(off)}			135		ns
Turn-Off Fall Time	t _f			140		ns

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051

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